HAMAMATSU



MPPC® (multi-pixel photon Counter)

S10362-33 series S10931 series

New type of Si photon-counting device, Active area: 3 × 3 mm

The MPPC is a new type of photon-counting device made up of multiple APD (avalanche photodiode) pixels operated in Geiger mode. The MPPC is an opto-semiconductor device with excellent photon-counting capability and which also possesses great advantages such as low voltage operation and insensitivity to magnetic fields.

Features

- Excellent photon-counting capability (excellent detection efficiency versus number of incident photons)
- → Room temperature operation
- **■** Low bias (below 100 V) operation
- High gain: 105 to 106
- Insensitive to magnetic fields
- Excellent time resolution
- Compact size
- **■** Simple readout circuit operation

- Applications

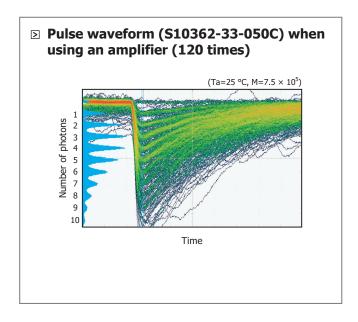
- **➡** Fluorescence measurement
- **➡** Biological flow cytometry
- DNA BIO-chip sequencer
- **■** Environmental analysis
- **→ PET**
- **→** High-energy physics experiments

Feature 01 What is the MPPC?

The MPPC is a kind of so-called Si-PM (silicon photomultiplier) device. It is a photon-counting device consisting of multiple APD pixels operating in Geiger mode. Each APD pixel of the MPPC outputs a pulse signal when it detects one photon. The signal output from the MPPC is the total sum of the outputs from all APD pixels. The MPPC offers the high performance needed in photon counting and is used in diverse applications for detecting-extremely weak light at the photon-counting level.

Feature 02 Excellent photon counting capability

The MPPC delivers superb photon-counting performance. Connecting the MPPC to an amplifier will show sharp waveforms on an oscilloscope according to the number of detected photons.



Selection guide

| Parameter | Symbol | S10362-33 | | | S10931 | | | Unit |
|-----------------------|--------|-----------|---------|-----------|---------|---------|-----------|-------|
| | | -025C | -050C | -100C | -025P | -050P | -100P | Offic |
| Effective active area | - | | 3 × 3 | | | 3 × 3 | | mm |
| Number of pixels | - | 14400 | 3600 | 900 | 14400 | 3600 | 900 | - |
| Pixel size | - | 25 × 25 | 50 × 50 | 100 × 100 | 25 × 25 | 50 × 50 | 100 × 100 | μm |

- Absolute maximum ratings

| Parameter | Symbol | S10362-33 series | S10931 series | Unit |
|-----------------------|--------|------------------|---------------|------|
| Operating temperature | Topr | -20 to 40 | 0 to 40 | °C |
| Storage temperature | Tstg | -20 to 60 | -20 to 60 | °C |

■ Electrical and optical characteristics (Typ. Ta=25 °C, unless otherwise noted)

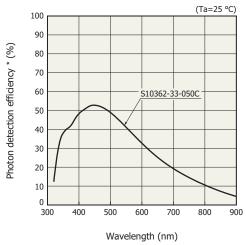
| Parameter | Symbol | S10362-33 | | | S10931 | | | Unit |
|--|--------|------------------------|---------------------|---------------------|------------------------|---------------------|---------------------|-------|
| | | -025C | -050C | -100C | -025P | -050P | -100P | UIIIL |
| Fill factor *1 | - | 30.8 | 61.5 | 78.5 | 30.8 | 61.5 | 78.5 | % |
| Spectral response range | λ | 320 to 900 | | | 320 to 900 | | | nm |
| Peak sensitivity wavelength | λр | 440 | | | 440 | | | nm |
| Operating voltage range | - | 70 ± 10 * ² | | | 70 ± 10 * ² | | | V |
| Dark count *3 | - | 4 | 6 | 8 | 4 | 6 | 8 | Mcps |
| Dark count Max. *3 | - | 8 | 10 | 12 | 8 | 10 | 12 | Mcps |
| Terminal capacitance | Ct | 320 | | | 320 | | | pF |
| Time resolution (FWHM) *4 | - | 500 to 600 | | | 500 to 600 | | | ps |
| Temperature coefficient of reverse voltage | - | 56 | | | 56 | | | mV/°C |
| Gain | М | 2.75×10^{5} | 7.5×10^{5} | 2.4×10^{6} | 2.75×10^{5} | 7.5×10^{5} | 2.4×10^{6} | - |

^{*1:} Ratio of the active area of a pixel to the entire area of the pixel

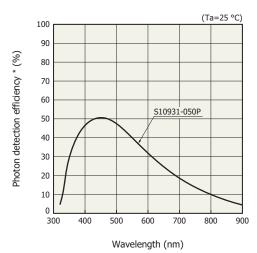
Note: Each value was measured at recommended operating voltage.

The last letter of each type number indicates package materials (C: ceramic, P: SMD).

Photon detection efficiency (PDE) vs. wavelength (typical example)



^{*} Photon detection efficiency includes effects of crosstalk and afterpulses.



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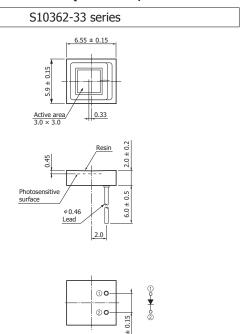
KAPDB0173EA KAPDB0174EA

^{*2:} For the recommended operating voltage of each product, refer to the data attached to each product.

^{*3: 0.5} p.e. (threshold level)

^{*4:} Single photon level

Dimensional outlines (unit: mm, tolerance: ±0.1 mm unless otherwise noted)



S10931 series

0.925 ± 0.15

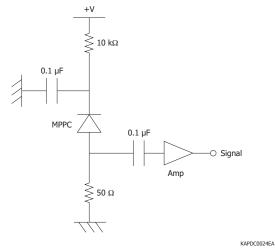
Active area
3.0 × 3.0

Photosensitive surface

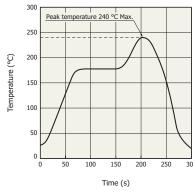
Index mark \$\phi 0.2

KAPDA0123EB

- Connection example



Recommended solder reflow condition (S10931-025P/-050P/-100P)



- · After unpacking, store this device in an environment at a temperature of 25 °C and a humidity below 60%, and perform reflow soldering on this device within 24 hours.
- Thermal stress applied to the device during reflow soldering differs depending on the PC boards and reflow oven being used.
- · When setting the reflow conditions, make sure that the reflow soldering process does not degrade device reliability.

Precautions for use

- Install an appropriate protection circuit for the power supply, equipment, and measuring instrument according to the application, in order to prevent overvoltage and overcurrent damage.
- Recommended soldering conditions (S10362-33 series)
 - · Temperature of soldering iron tip: 350 °C Max.
 - · Soldering time: 3 s Max.
 - · Soldering Point: at least 1 mm away from the root of the terminal
 - · Times: once

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